TITLE OF INVENTION: SUBSTRATE PROCESSING METHOD AND SUBSTRATE PROCESSING APPARATUS

ABSTRACT

A substrate processing method includes accommodating a substrate having a space, wherein a wall surface forming the space has a target film; a first process of supplying a first gas to the substrate; a second process of exhausting the processing container; a third process of supplying a second gas to the substrate, which reacts with the target film together with the first gas to generate a reaction product on the wall surface; a fourth process of exhausting the processing container; a reaction process of repeating a cycle of sequentially performing the first to third processes, and the fourth process so as to generate the reaction product, and of setting a temperature of the substrate to a first temperature; and a removal process of removing the reaction product by setting the temperature of the substrate after the reaction process to a second temperature higher than the first temperature.

(Fig. 12)